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Fairchild Semiconductor FDA28N50

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May 2014



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FDA28N50

N-Channel UniFETTM MOSFET 500 V, 28 A, 155 m Ω

Features

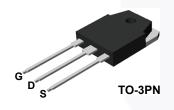
- $R_{DS(on)}$ = 122 $m\Omega$ (Typ.) @ V_{GS} = 10 V, I_D = 14 A
- Low Gate Charge (Typ. 80 nC)
- Low C_{rss} (Typ. 42 pF)
- 100% Avalanche Tested
- · RoHS Compliant

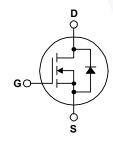
Applications

- PDP TV
- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDA28N50	Unit	
V _{DSS}	Drain to Source Voltage			500	V	
V _{GSS}	Gate to Source Voltage			±30	V	
1	Drain Current	- Continuous (T _C = 25°C)		28	А	
I _D Drain Current		- Continuous (T _C = 100°C)		17	A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	112	Α	
E _{AS}	Single Pulsed Avalanche En	ergy	(Note 2)	2391	mJ	
I _{AR}	Avalanche Current		(Note 1)	28	Α	
E _{AR}	Repetitive Avalanche Energy	1	(Note 1)	31	mJ	
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	5	V/ns	
D	Dower Discinction	$(T_C = 25^{\circ}C)$		310	W	
P_{D}	Power Dissipation	- Derate Above 25°C		2.5	W/°C	
T _J , T _{STG}	Operating and Storage Temp	perature Range		-55 to +150	°C	
TL	Maximum Lead Temperature	for Soldering, 1/8" from Case for 5 Sec	onds	300	οС	

Thermal Characteristics

Symbol	Parameter FDA28N50		Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	- C/VV



Datasheet of FDA28N50 - MOSFET N-CH 500V 28A TO-3PN

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Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDA28N50	FDA28N50	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Chara	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	500	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.59	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V	-	-	1	μА
IDSS	Zero Gate Voltage Drain Guirent	$V_{DS} = 400 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μΑ
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 14 A	-	0.122	0.155	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 14 A	-	34	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V = 25 V V = 0 V	-	3866	5140	pF
Coss	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		576	766	pF
C _{rss}	Reverse Transfer Capacitance	1 111112	-\	42	63	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 400 V, I _D = 28 A,	- \	80	105	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	21	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note	4) _	32	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	56	122	ns
t _r		$V_{DD} = 250 \text{ V}, I_D = 28 \text{ A},$	-	126	262	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 25 Ω	-	210	430	ns
t _f	Turn-Off Fall Time	(Note 4)	-	110	230	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	28	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Fo	orward Current	< <u>-</u>	-	112	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 28 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 28 A,	-	530	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	8	_	μС

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 6.1 mH, I $_{AS}$ = 28 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C.
- 3. I $_{SD} \leq$ 28 A, di/dt \leq 200 A/µs, V $_{DD} \leq$ BV $_{DSS},$ starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.



Typical Performance Characteristics

Figure 1. On-Region Characteristics

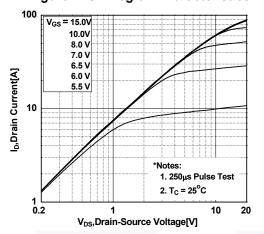


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

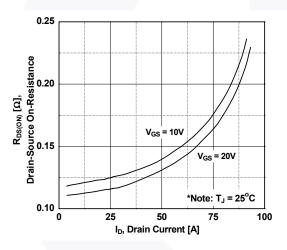


Figure 5. Capacitance Characteristics

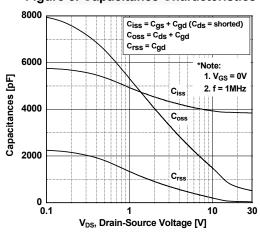


Figure 2. Transfer Characteristics

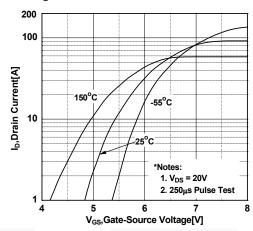


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

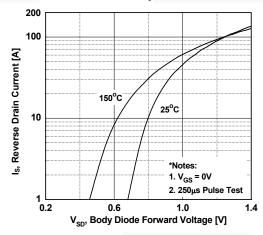
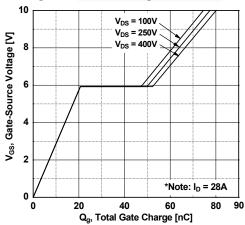


Figure 6. Gate Charge Characteristics





Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

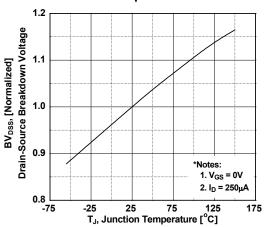


Figure 8. On-Resistance Variation vs. Temperature

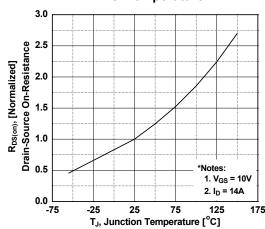


Figure 9. Maximum Safe Operating Area

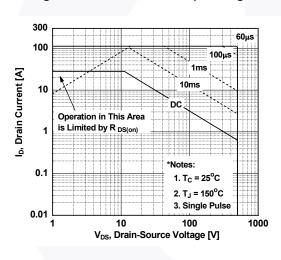


Figure 10. Maximum Drain Current vs. Case Temperature

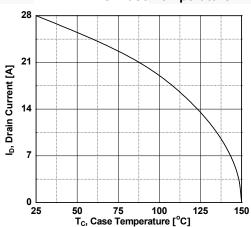
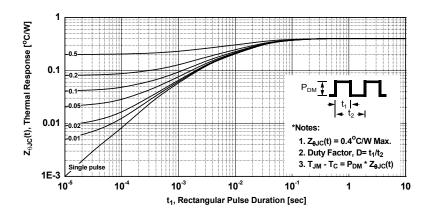


Figure 11. Transient Thermal Response Curve



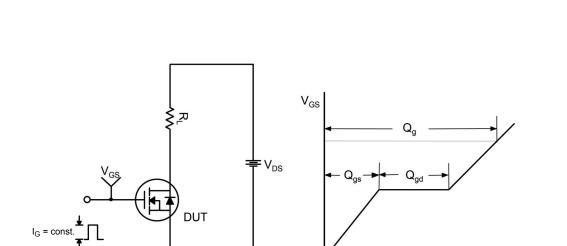


Figure 12. Gate Charge Test Circuit & Waveform

Charge

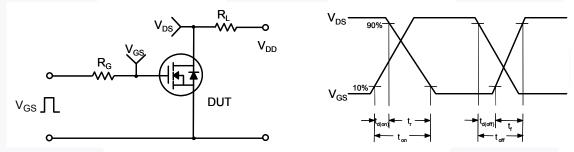


Figure 13. Resistive Switching Test Circuit & Waveforms

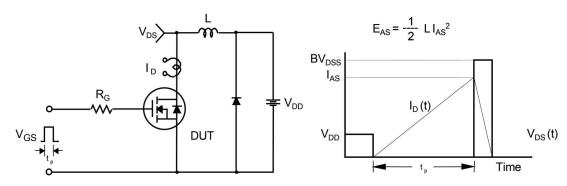
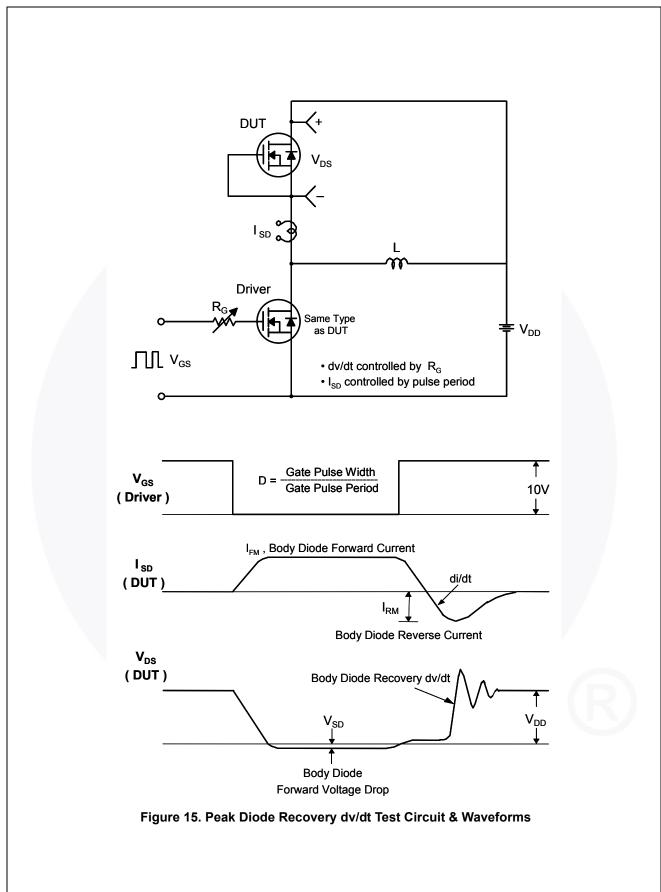
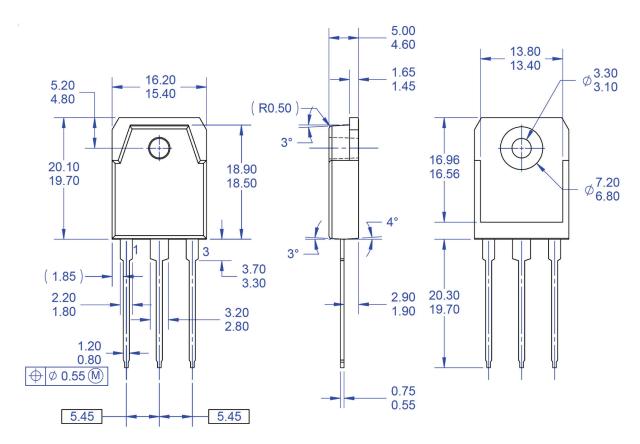
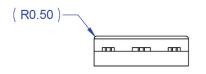


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions





NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ
- SC-65 PACKAGING STANDARD. ALL DIMENSIONS ARE IN MILLIMETERS. DIMENSION AND TOLERANCING PER ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS. DRAWING FILE NAME: TO3PN03AREV1.
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Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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